VS-UFB80FA60

Vishay Semiconductors

Insulated Ultrafast Rectifier Module, 80 A



SOT-227

PRIMARY CHARACTERISTICS						
V _R	600 V					
$I_{F(AV)}$ per module at $T_C = 104 \text{ °C}$	80 A					
t _{rr}	34 ns					
Туре	Modules - diode FRED Pt [®]					
Package	SOT-227					

FEATURES

- Two fully independent diodes
- Fully insulated package
- Ultrafast, soft reverse recovery, with high COMPLIANT operation junction temperature (T_J max. = 175 °C)
- Low forward voltage drop
- Optimized for power conversion: welding and industrial SMPS applications
- Easy to use and parallel
- Industry standard outline
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

The VS-UFB80FA60 insulated modules integrate two state of the art ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The diodes structure, and its life time control, provide an ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, DC/DC converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Cathode to anode voltage	V _R		600	V		
Continuous forward current per diode	I _F	T _C = 85 °C	57	^		
Single pulse forward current per diode	I _{FSM}	T _C = 25 °C	280	A		
Maximum power dissipation per module	PD	T _C = 85 °C	174	W		
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 min	2500	V		
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C		

ELECTRICAL SPECIFICATIONS PER DIODE ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
Forward voltage	V _{FM}	I _F = 30 A	-	1.32	1.69		
		I _F = 60 A	-	1.52	1.9	V	
		I _F = 30 A	T.I = 125 °C	-	1.14	1.39	
		I _F = 60 A	1j = 125 C	-	1.38	1.66	
Reverse leakage current		$V_R = V_R$ rated	-	0.1	50	μA	
neverse leakage current	I _{RM}	$T_J = 175 \text{ °C}, V_R = V_R \text{ rated}$		-	0.2	1.0	mA
Junction capacitance	CT	V _R = 600 V		-	30	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL		TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
		T _J = 25 °C	$I_F=1~A,~dI_F/dt=200~A/\mu s,~V_R=30~V$	-	34	-	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	79	-	ns
		T _J = 125 °C	1 20 4	-	155	-	
Book rocovery ourrept	1	T _J = 25 °C	I _F = 30 A dI _F /dt = 200 A/μs	-	6	-	А
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm B} = 200 \text{ V}$	-	14	-	A
	T _J = 25 °C	v _R – 200 v	-	234	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1085	-	nc

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Junction to case, single leg conducting	Р		-	-	1.02		
Junction to case, both leg conducting	R _{thJC}		-	-	0.51	°C/W	
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.10	-		
Weight			-	30	-	g	
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)	
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)	
Case style			SOT-227				

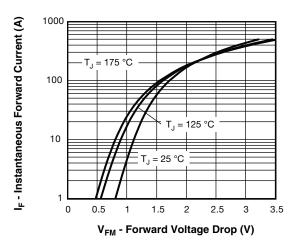


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Diode)

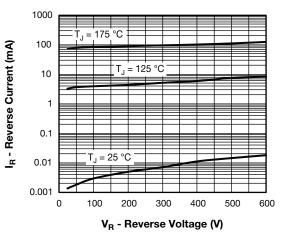
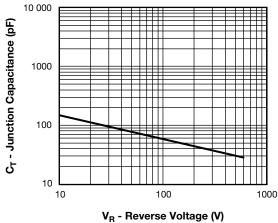
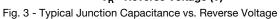


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

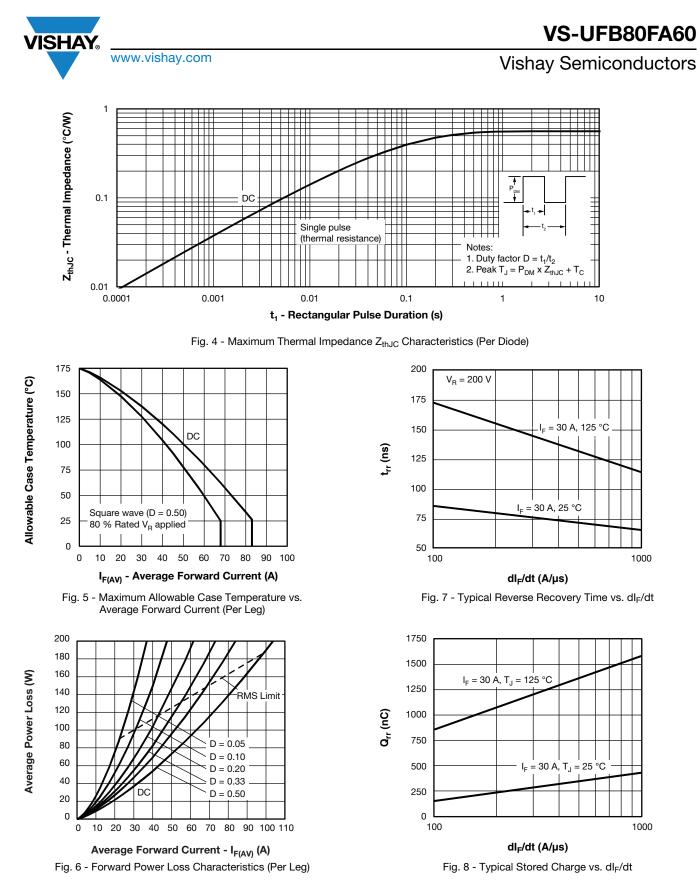




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Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V_{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see fig. 6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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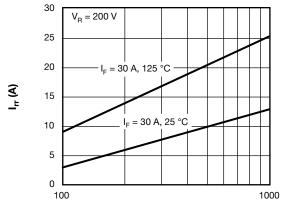
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dl_F/dt (A/µs)

Fig. 9 - Typical Stored Current vs. dl_F/dt

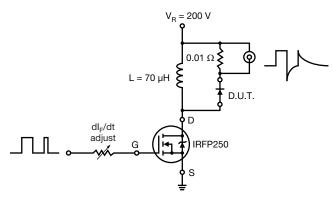
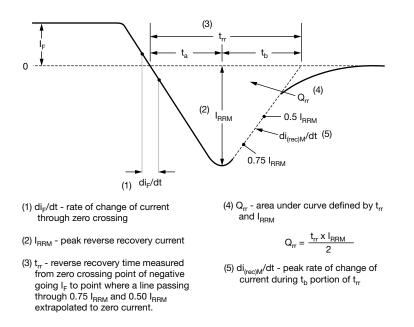
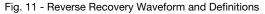


Fig. 10 - Reverse Recovery Parameter Test Circuit









ORDERING INFORMATION TABLE

Device code	VS-	UF	в	80	F	A	60
		2	3	4	5	6	7
	1 -	Visl	nay Sen	niconduc	ctors pro	oduct	
	2 -	Ultr	afast re	ctifier			
	3 -	Ultr	afast Pt	diffused			
	4 -	Cur	rent rati	ng (80 =	80 A)		
	5 -	Circ	cuit conf	iguratior	n (two se	eparate	diodes
	6 -	Pac	kage in	dicator (SOT-22	27 stanc	lard ins
	7 -	Vol	tage rati	ng (60 =	= 600 V))	

CIRCUIT CONFI	CIRCUIT CONFIGURATION							
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING						
Two separate diodes, parallel pin-out	F	Lead Assignment						

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95423				
Packaging information	www.vishay.com/doc?95425				

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SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

• Controlling dimension: millimeter



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